

Notice of References Cited	Application/Control No. 10/514,429		Applicant(s)/Patent Under Reexamination DWILINSKI ET AL.	
	Examiner MICHAEL J. LOGIE		Art Unit 2881	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,051,145 A	04-2000	Griffith et al.	210/761
*	B	US-6,265,322 B1	07-2001	Anselm et al.	438/745
*	C	US-6,270,569 B1	08-2001	Shibata et al.	117/68
*	D	US-6,303,403 B1	10-2001	Sato et al.	438/29
*	E	US-2002/0063258 A1	05-2002	MOTOKI, KENSAKU	257/95
*	F	US-6,531,072 B1	03-2003	Suda et al.	252/301.4R
*	G	US-6,534,795 B2	03-2003	Hori et al.	257/79
*	H	US-2003/0209191 A1	11-2003	Purdy, Andrew P.	117/84
*	I	US-2004/0031978 A1	02-2004	D'Evelyn et al.	257/233
*	J	US-6,720,586 B1	04-2004	Kidoguchi et al.	257/103
*	K	US-7,097,707 B2	08-2006	Xu, Xueping	117/13
*	L	US-7,291,544 B2	11-2007	D'Evelyn et al.	438/478
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	FR 2796657 A1	01-2001	France	DEMAZEAU et al.	C30B 11/00
	O	WO 01/24284 A1	04-2001	PCT	Mueller-Mach et al.	H01L 33/00
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Motoki, Kensaku et al. (2001). "Preparation of Large Freestanding GaN Substrates by Hydride Vapor Phase Epitaxy Using GaAs as a starting Substrate," J. Appl. Phys. 40:L140-L143.
	V	R. Dwilinski et al. (1998). "AMMONO Method of GaN and AlN Production," Diamond and Related Materials Vol. 7: Pages 1348-1350
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.